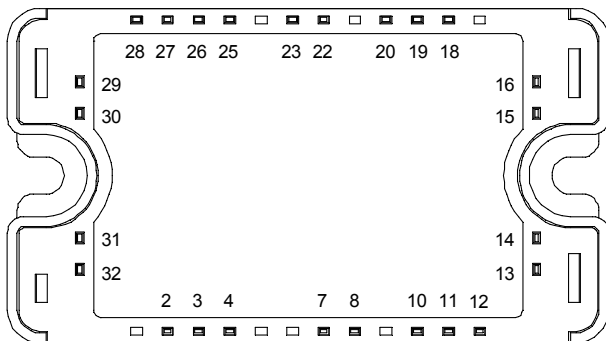
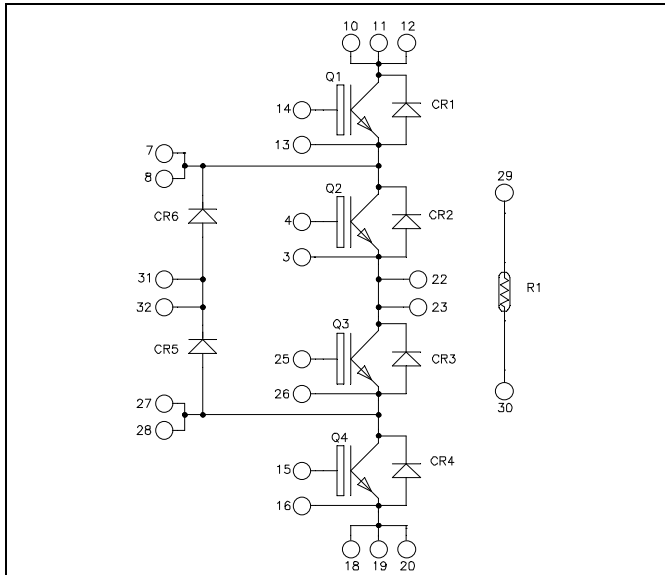


*Three level inverter
NPT IGBT Power Module*

**$V_{CES} = 600V$
 $I_C = 30A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
 Example: 10/11/12 ; 7/8 ...

Application

- Solar converter
- Uninterruptible Power Supplies

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Q1 to Q4 Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	42
		$T_c = 80^\circ C$	30
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	140
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	60A@500V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
 See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Q1 to Q4 Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 600V$	$T_j = 25^\circ\text{C}$			250	μA
			$T_j = 125^\circ\text{C}$			500	
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 30A$	$T_j = 25^\circ\text{C}$	1.7	2.0	2.45	V
			$T_j = 125^\circ\text{C}$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE2}, I_C = 1mA$	4		6	V	
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA	

Q1 to Q4 Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$		1350		pF
C_{oes}	Output Capacitance			193		
C_{res}	Reverse Transfer Capacitance			120		
Q_g	Total gate Charge	$V_{GE} = 15V$ $V_{Bus} = 300V$ $I_C = 30A$		99		nC
Q_{ge}	Gate – Emitter Charge			10		
Q_{gc}	Gate – Collector Charge			60		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 30A$ $R_G = 6.8\Omega$		30		ns
T_r	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			80		
T_f	Fall Time			15		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 30A$ $R_G = 6.8\Omega$		32		ns
T_r	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			90		
T_f	Fall Time			21		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 30A$ $R_G = 6.8\Omega$	$T_j = 125^\circ\text{C}$		0.3	mJ
E_{off}	Turn-off Switching Energy			$T_j = 125^\circ\text{C}$	0.8	
I_{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 360V$ $t_p \leq 10\mu s ; T_j = 125^\circ\text{C}$			135	A
R_{thJC}	Junction to Case Thermal Resistance				0.9	$^\circ\text{C/W}$

CR1 to CR6 diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C			25	μA
			T _j = 150°C			500	
I _F	DC Forward Current	T _c = 80°C			30		A
V _F	Diode Forward Voltage	I _F = 30A			1.8	2.2	V
		I _F = 60A			2.2		
		I _F = 30A	T _j = 125°C		1.5		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 400V di/dt = 200A/μs	T _j = 25°C		25		ns
			T _j = 125°C		160		
Q _{rr}	Reverse Recovery Charge				35		nC
					480		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 400V di/dt = 1000A/μs	T _j = 125°C		0.6		mJ
R _{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

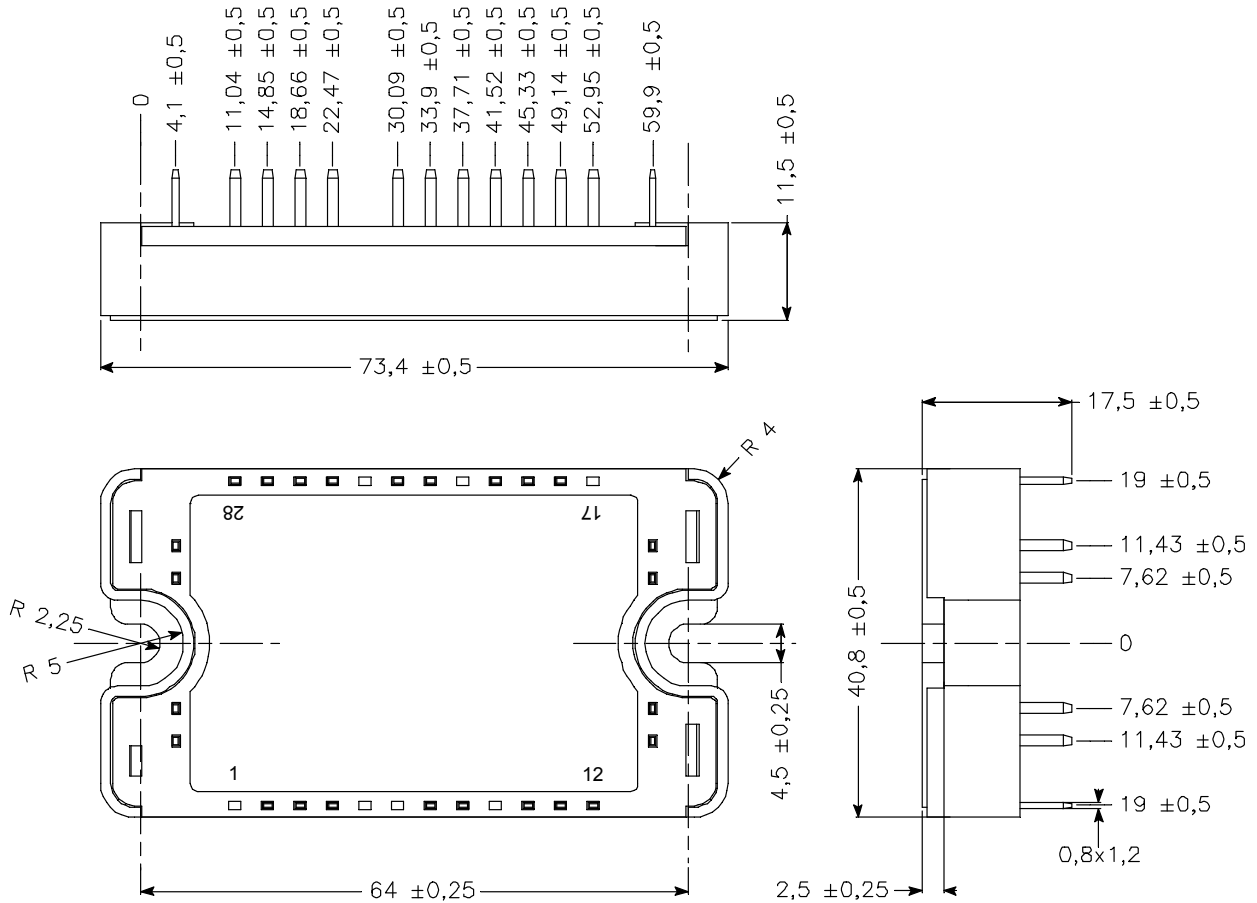
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

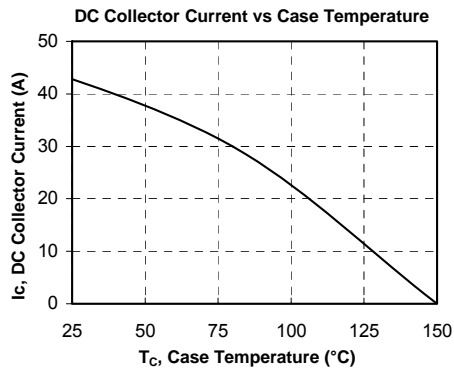
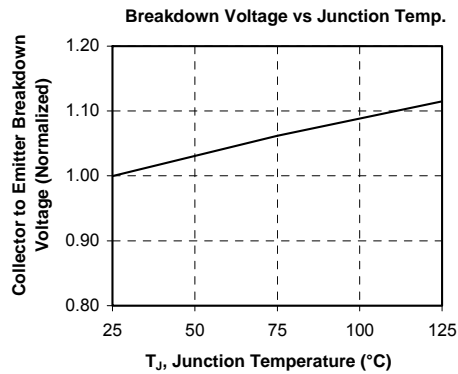
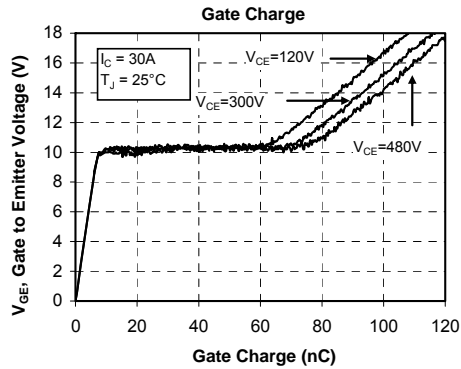
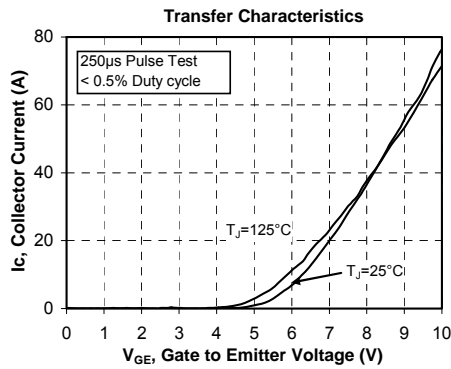
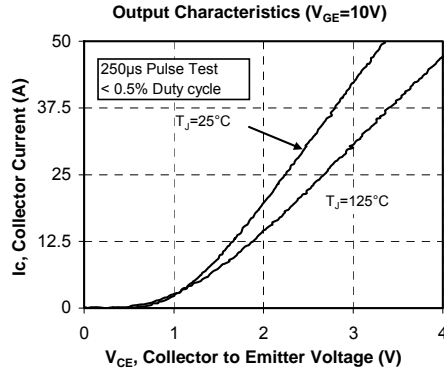
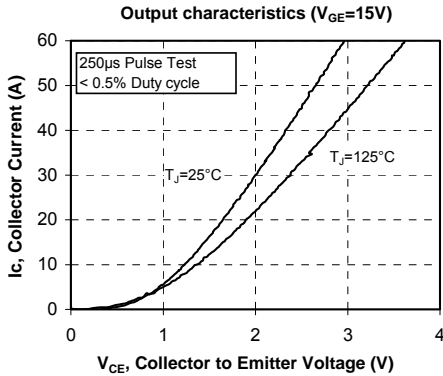
Symbol	Characteristic	Min	Typ	Max	Unit	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

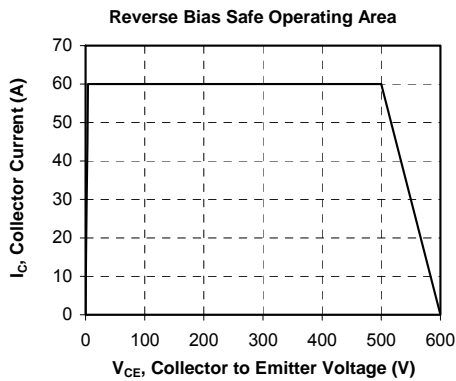
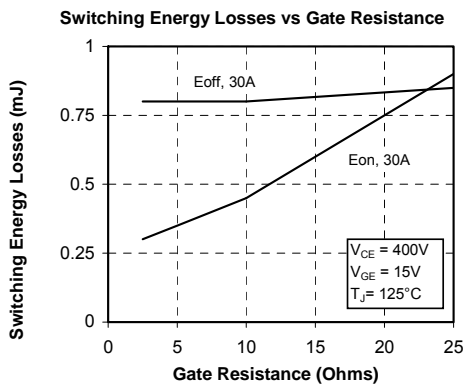
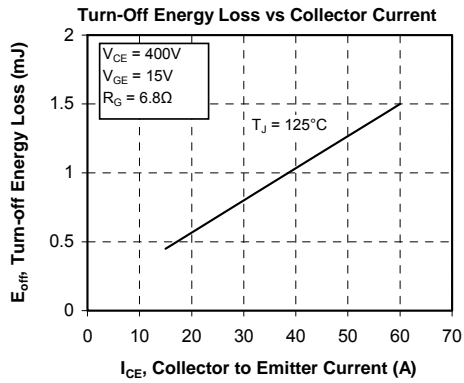
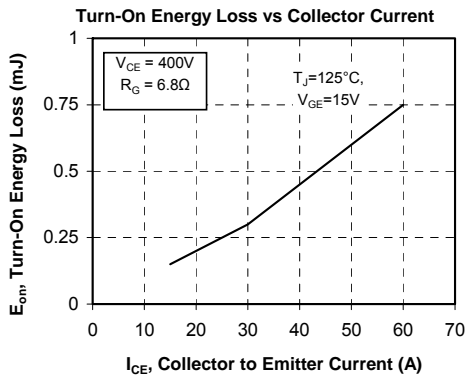
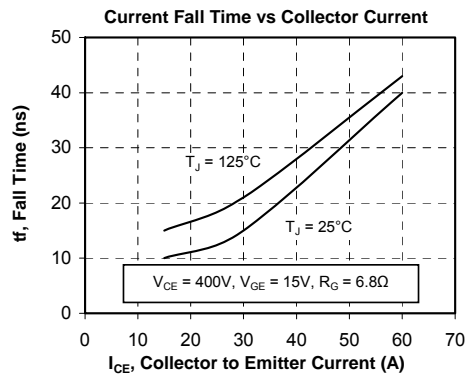
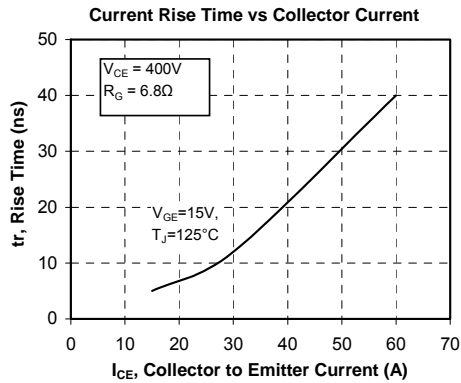
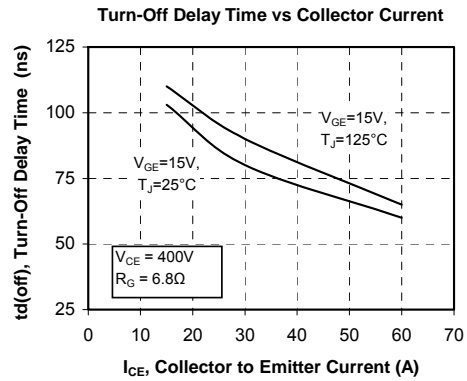
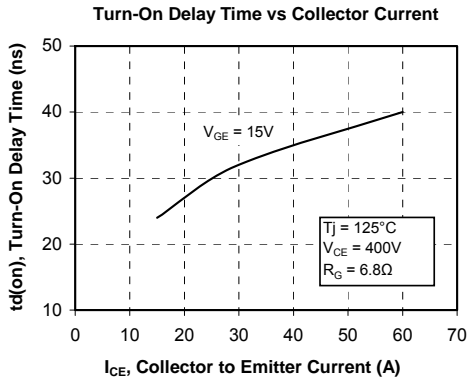
SP3 Package outline (dimensions in mm)

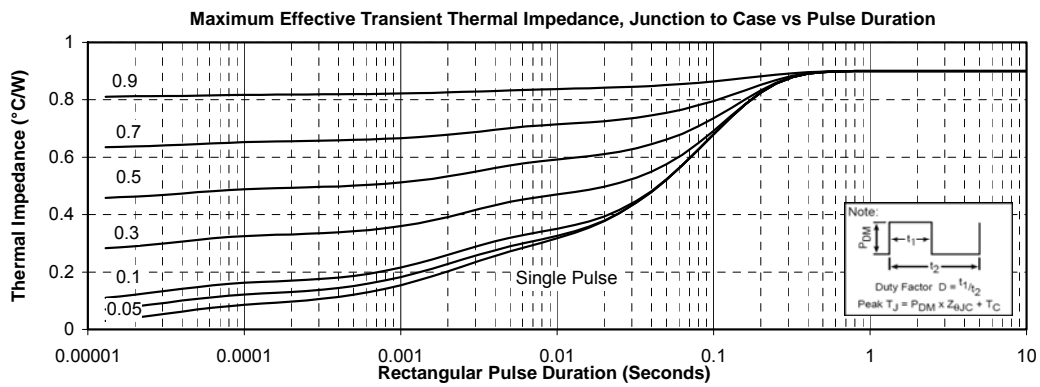
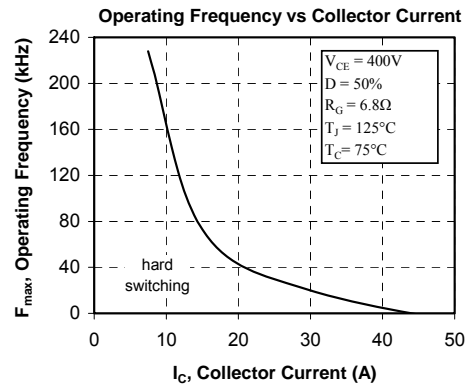
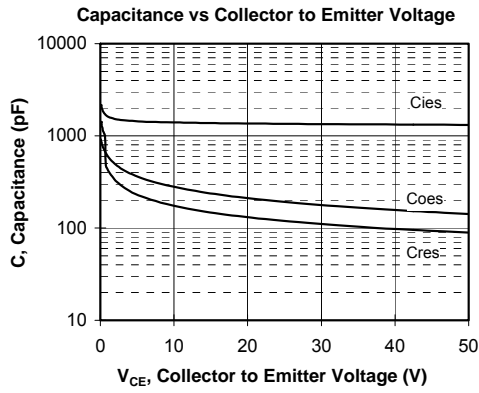


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

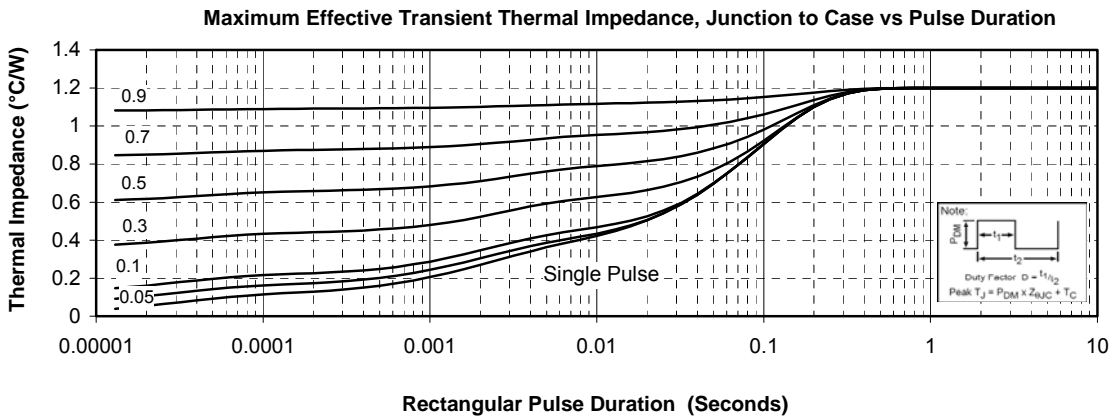
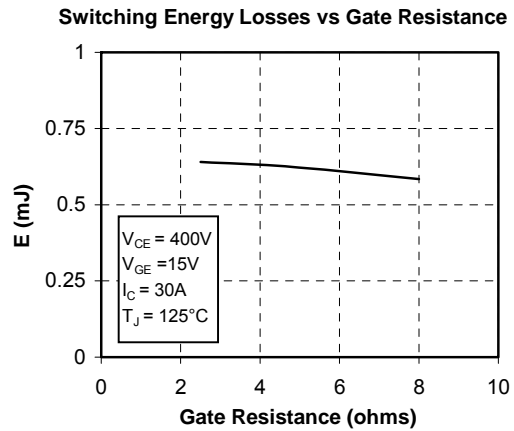
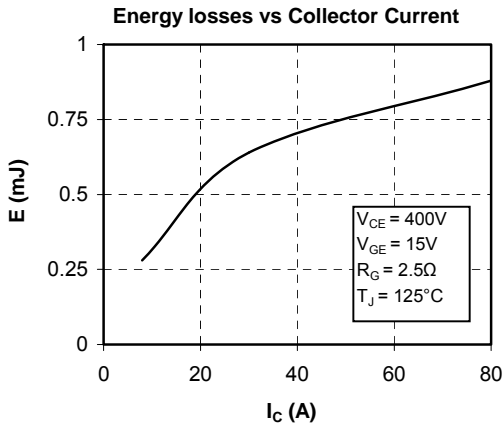
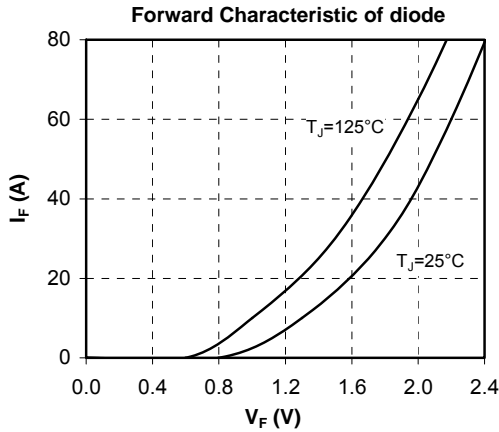
Q1 to Q4 Typical performance curve







CR1 to CR6 Typical performance curve



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